

AMENDMENTS TO THE SPECIFICATION

**I. Please replace the TITLE with the following amended
TITLE:**

**LAYOUT OF A THIN FILM TRANSISTOR AND THE FORMING
METHOD THEREOF**

**II. Please replace the paragraph on Page 12, lines 8 - 17, with
the following amended paragraph:**

In addition, if the present invention is applied to a transistor with its substrate 30 having a semiconductor layer 36, the semiconductor layer 36 may be upon the substrate 30 and electrically couples with the third conducting structure 33 and the fourth conducting structure 34 with the projection of ~~the sixth conducting structure 36~~ of the semiconductor layer 36 onto the substrate 30 totally inside the projection of the second conducting structure 32, as shown in FIG. 3D. By way of ~~described~~ the description above, the leakage current caused from light may be substantially declined for the declined probability that the semiconductor layer 36 is lighted, and hence substantially declined the probability that the performance of a transistor lowered by the leakage current caused from light.